

Supporting Information

Benign Role of Bi on Electrodeposited Cu₂O Semiconductor towards Photo-Assisted H₂ Generation from Water

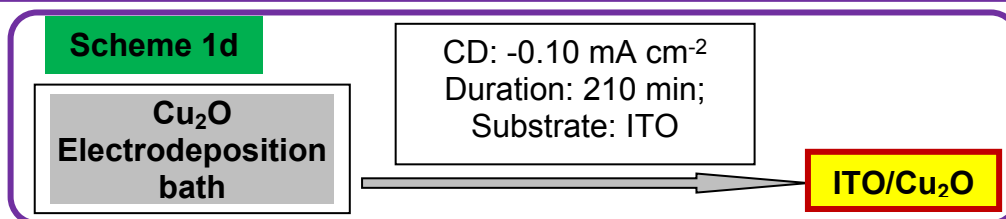
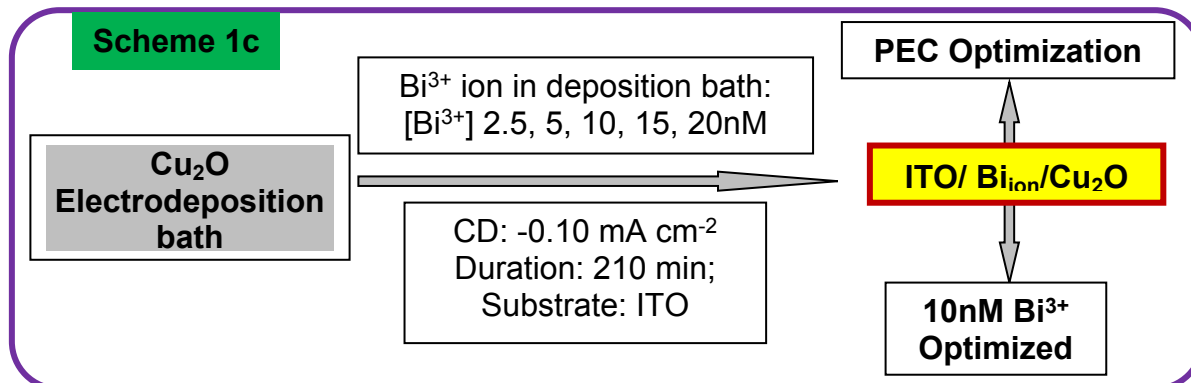
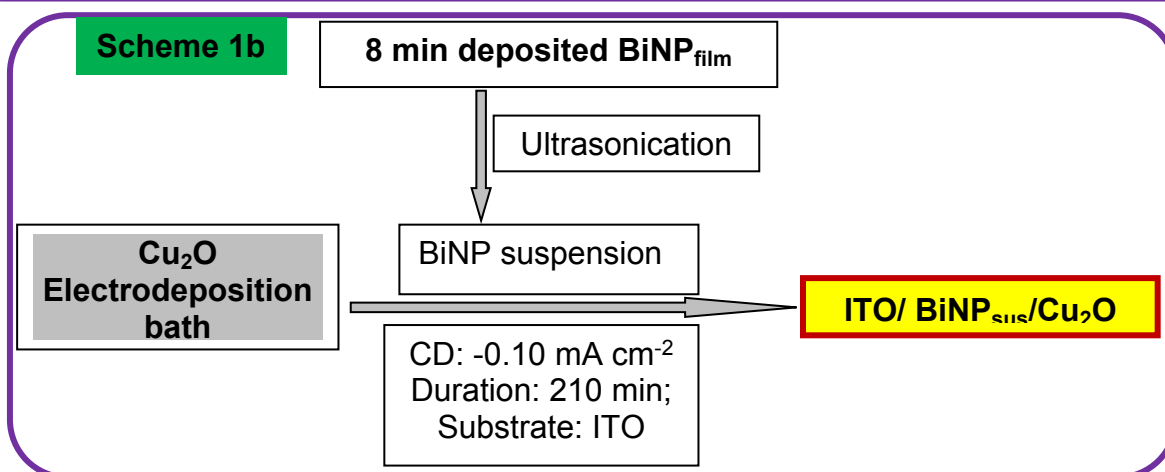
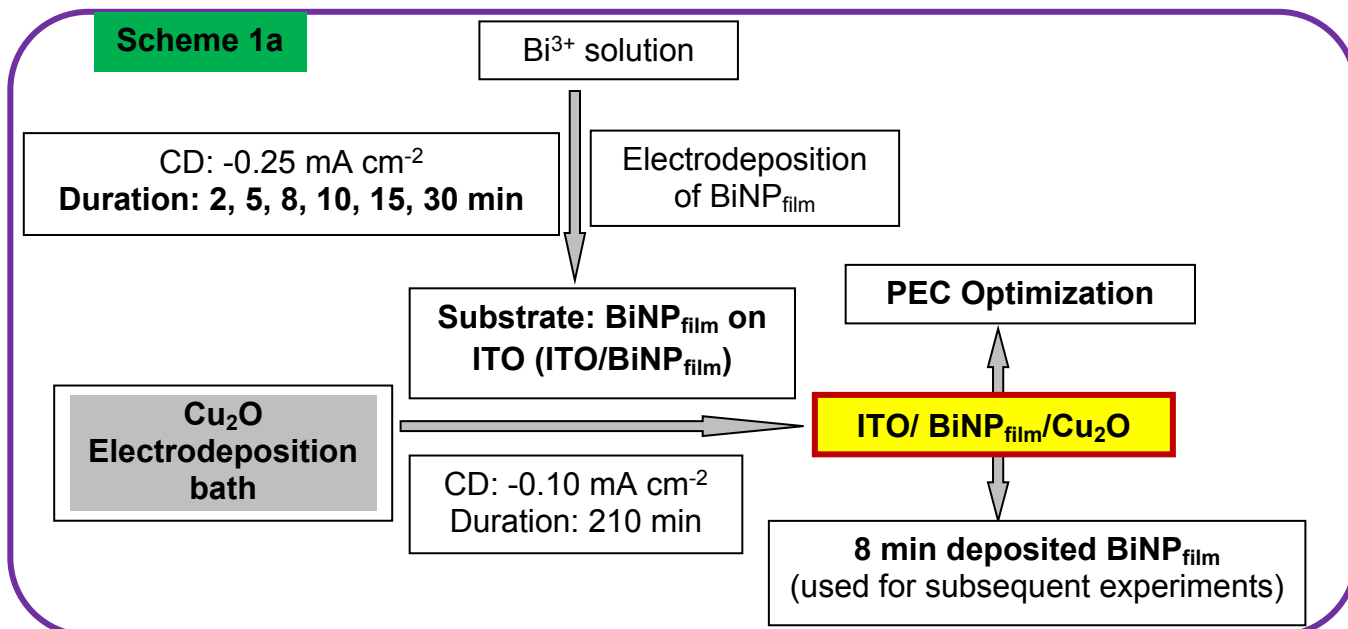
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Scheme 1(a-d): Electrodeposition of Cu₂O from different conditions.

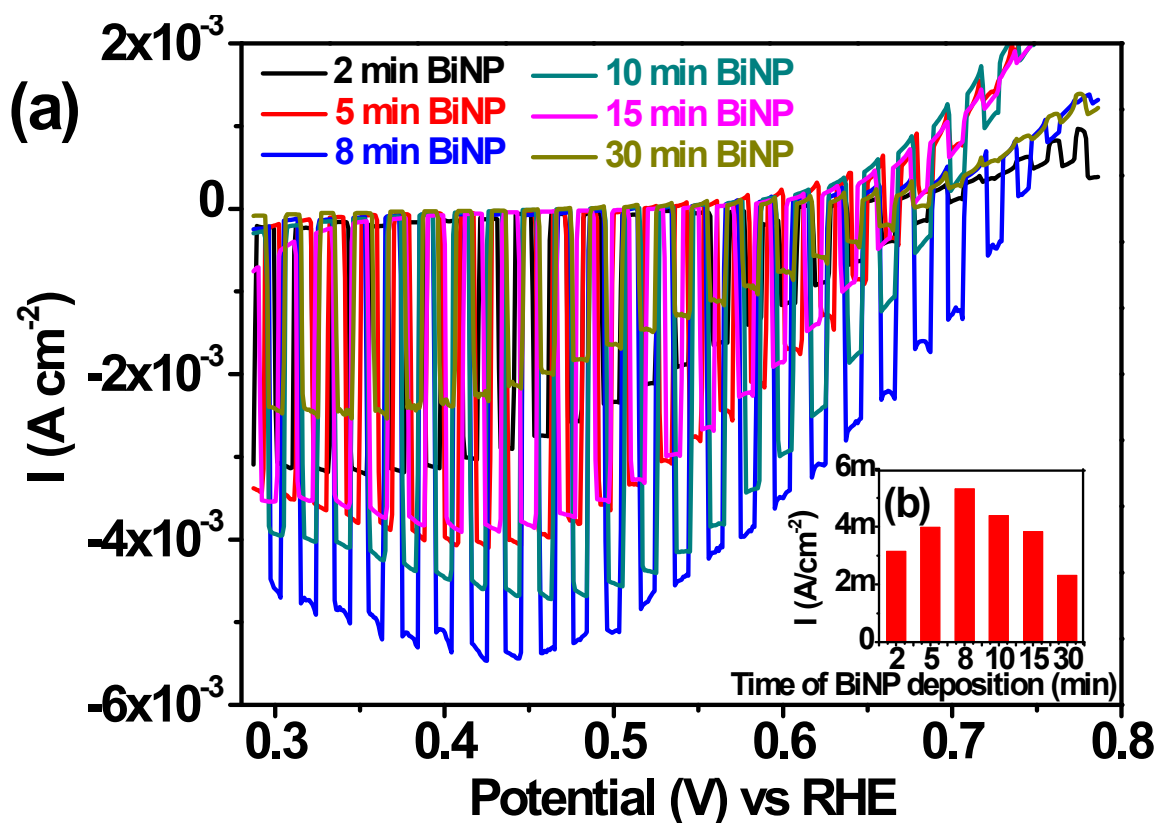


Fig. S1. (a) LSV plot in presence of 0.1 M Na_2SO_4 electrolyte (pH 4.9) under chopped light illumination of 35 mW cm^{-2} at a scan rate of 10 mV s^{-1} for optimization of deposition time of BiNPs film followed by Cu_2O deposition; **(b, Bar plot)** Variation of photo-generated current densities measured at a potential of 0.4 V vs RHE.

The optimized deposition time for BiNP film is 8 min. Cu_2O film developed over this film shows maximum photocurrent in photoelectrochemical reduction of water under illumination.

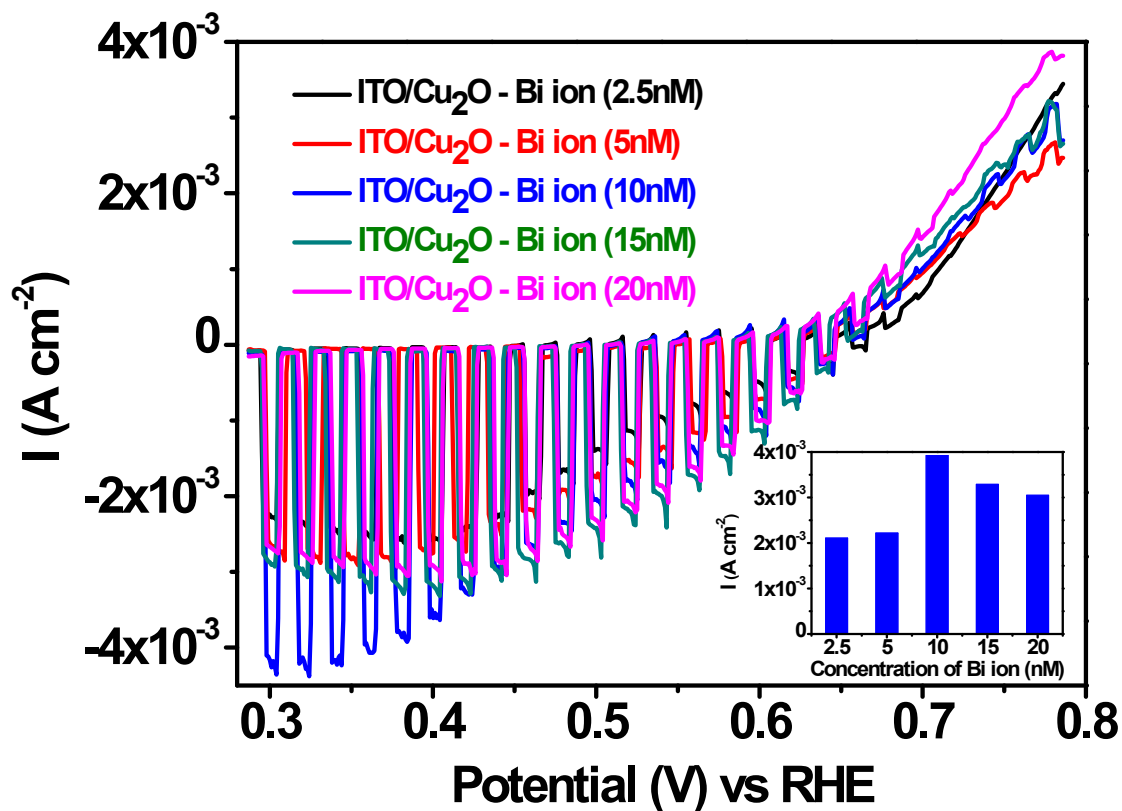


Fig. S2. (a) LSV plot in presence of 0.1 M Na₂SO₄ electrolyte (pH 4.9) under chopped light illumination of 35 mW cm⁻² at a scan rate of 10mV s⁻¹ for optimization of Bi³⁺ ions concentration in the Cu₂O electrodeposition bath. **(b, Bar plot)** Variation of photo-generated current densities measured at a potential of 0.4 V vs RHE.

The optimized Bi³⁺ ions concentration in Cu₂O electrodeposition bath is 10nM. Cu₂O film developed over this film shows maximum photocurrent in photoelectrochemical reduction of water under illumination.

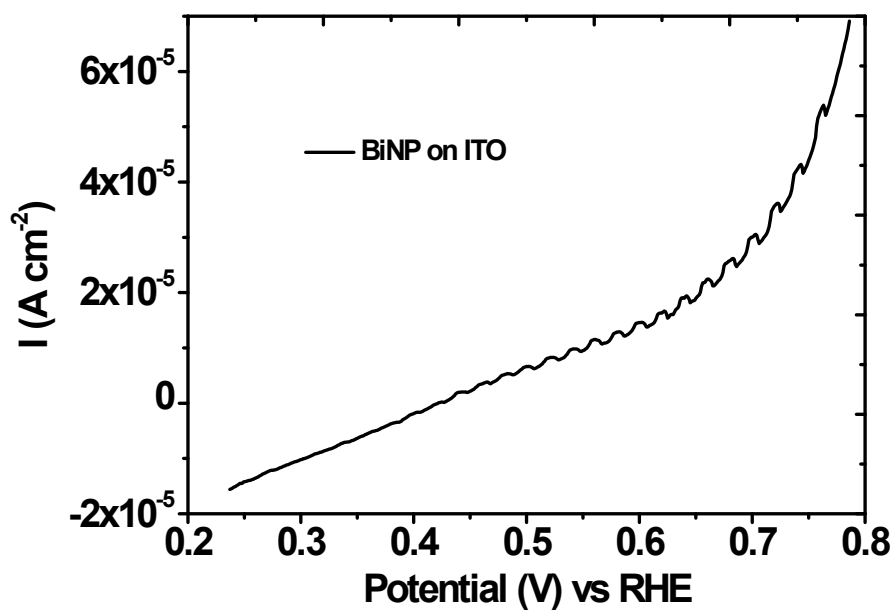


Fig. S3. LSV plot of BiNP on ITO in presence of 0.1 M Na₂SO₄ electrolyte (pH 4.9) under chopped light illumination of 35 mW cm⁻² at a scan rate of 10mV s⁻¹.

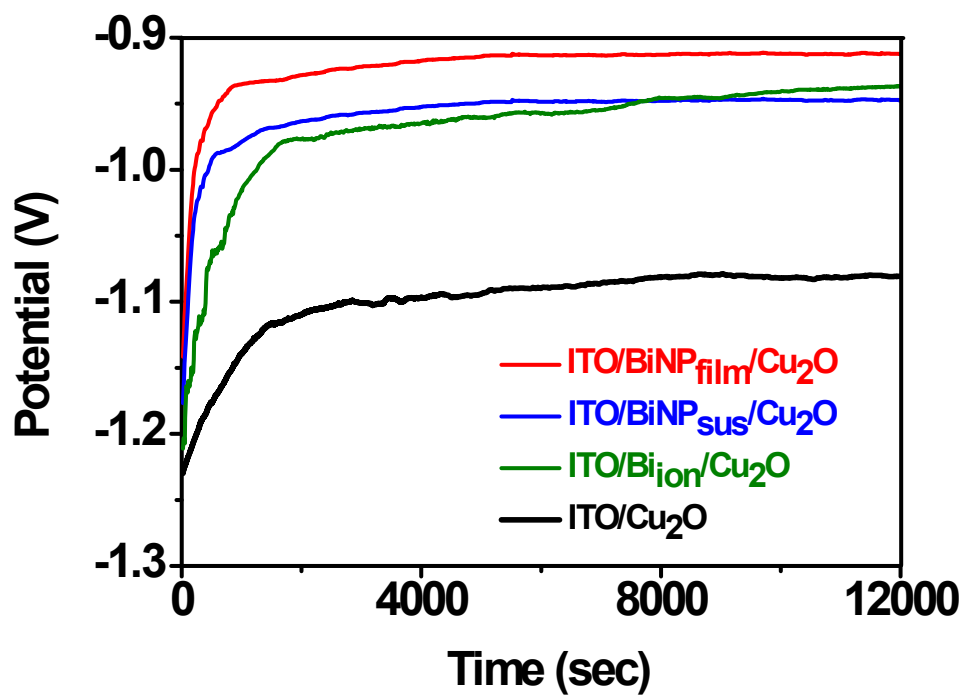


Fig. S4. Potential – Time curve during the deposition process of Cu₂O in different condition.

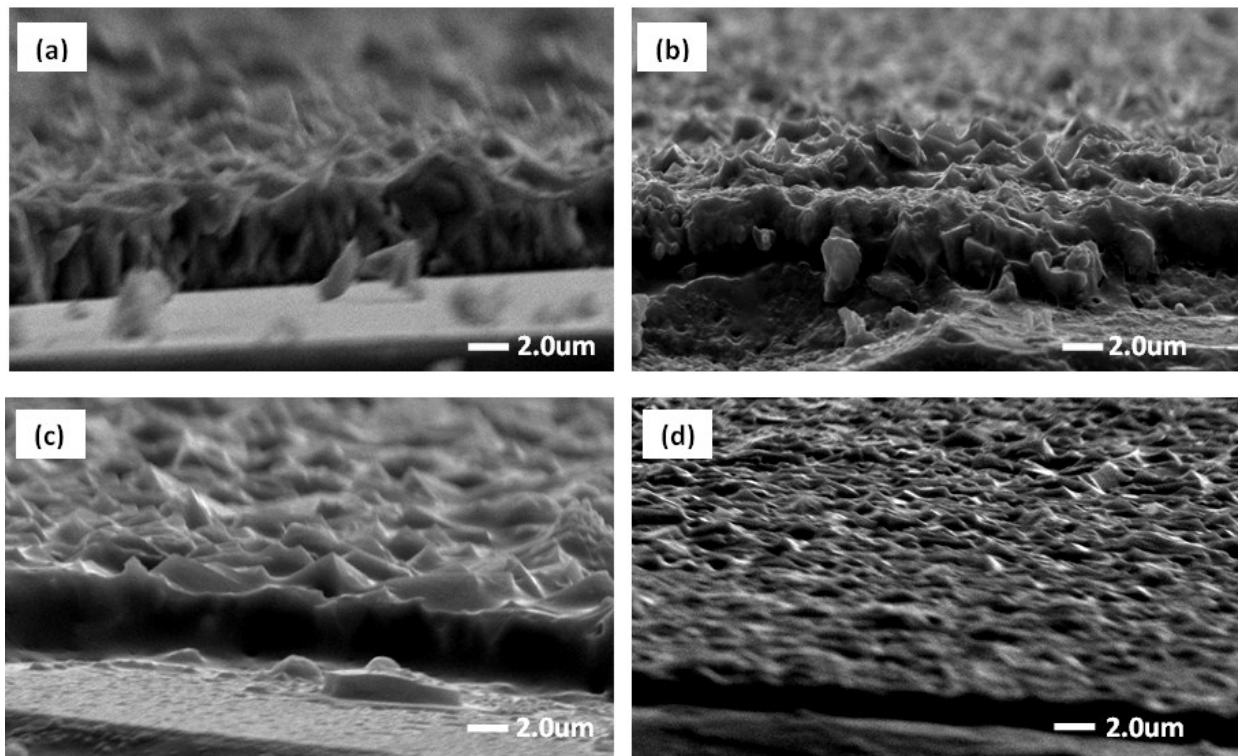


Fig. S5. Cross sectional SEM images of thin film semiconductor **(a)** ITO/BiNP_{film}/Cu₂O, **(b)** ITO/BiNP_{sus}/Cu₂O, **(c)** ITO/Bi_{ion}/Cu₂O, and **(d)** ITO/Cu₂O.

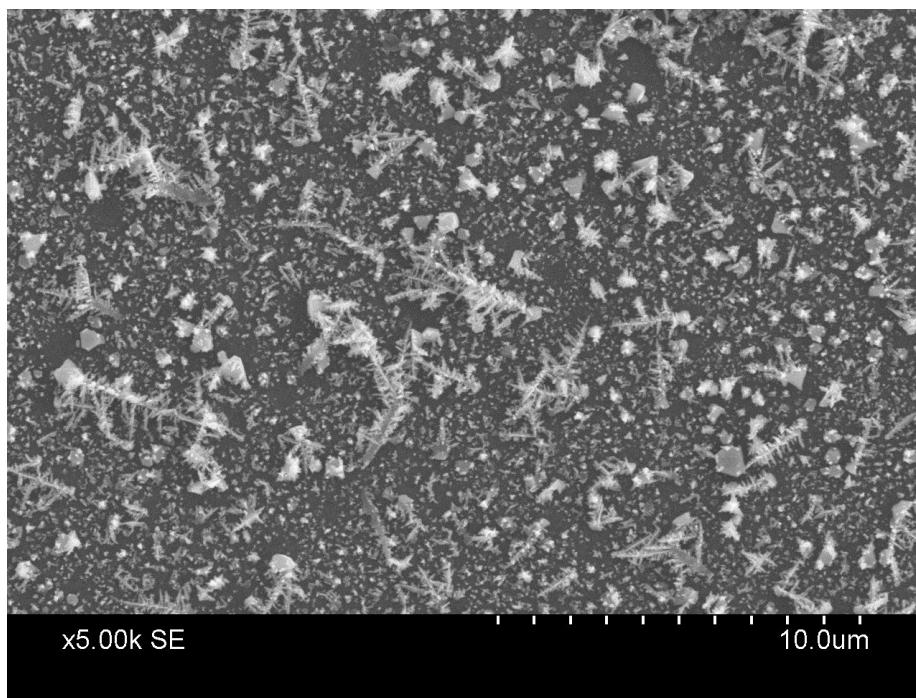


Fig. S6. SEM image of the BiNP film on ITO glass substrate.

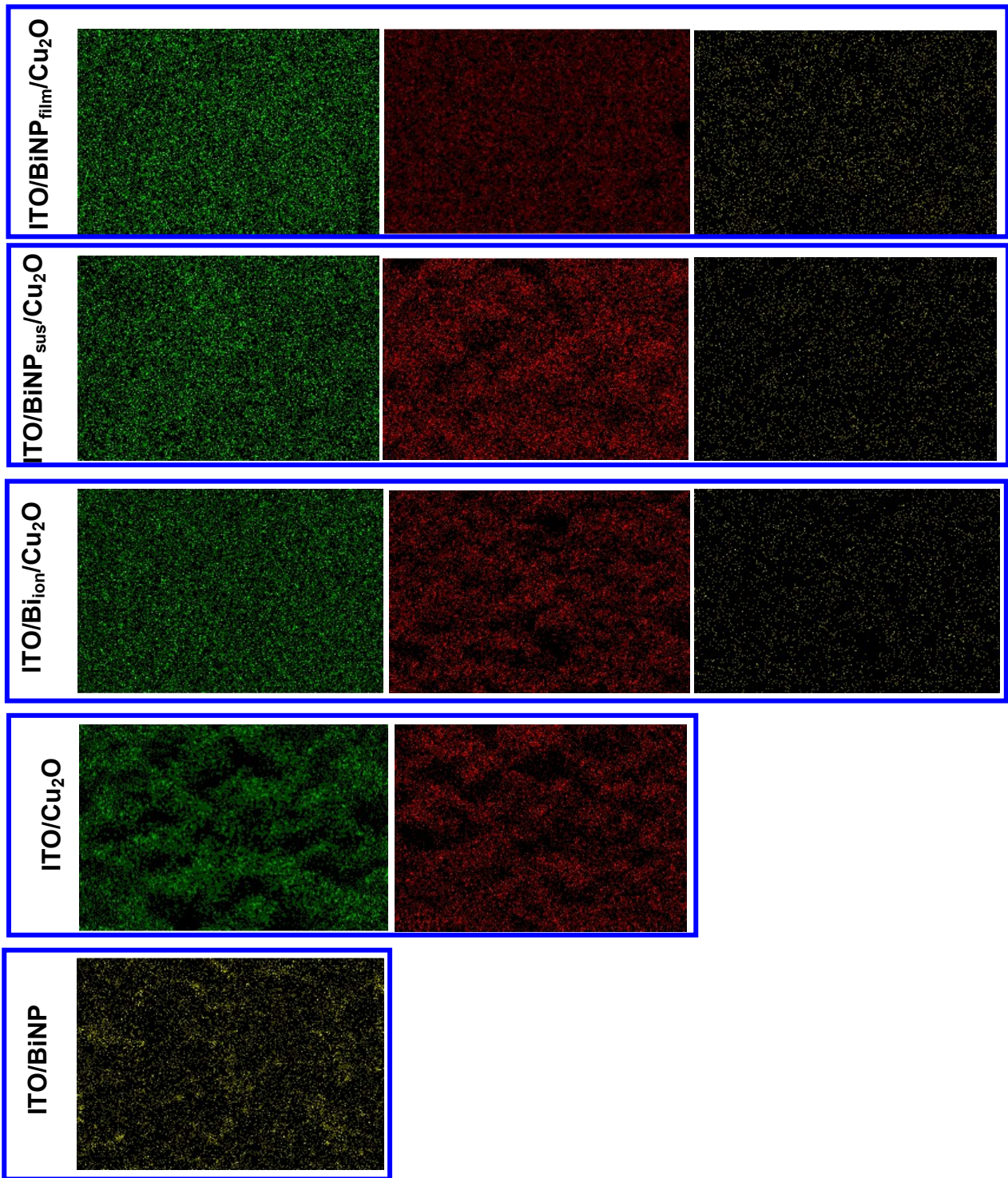


Fig. S7. Elemental mapping of Cu (Green), O (Red), and Bi (Yellow) obtained from different samples.

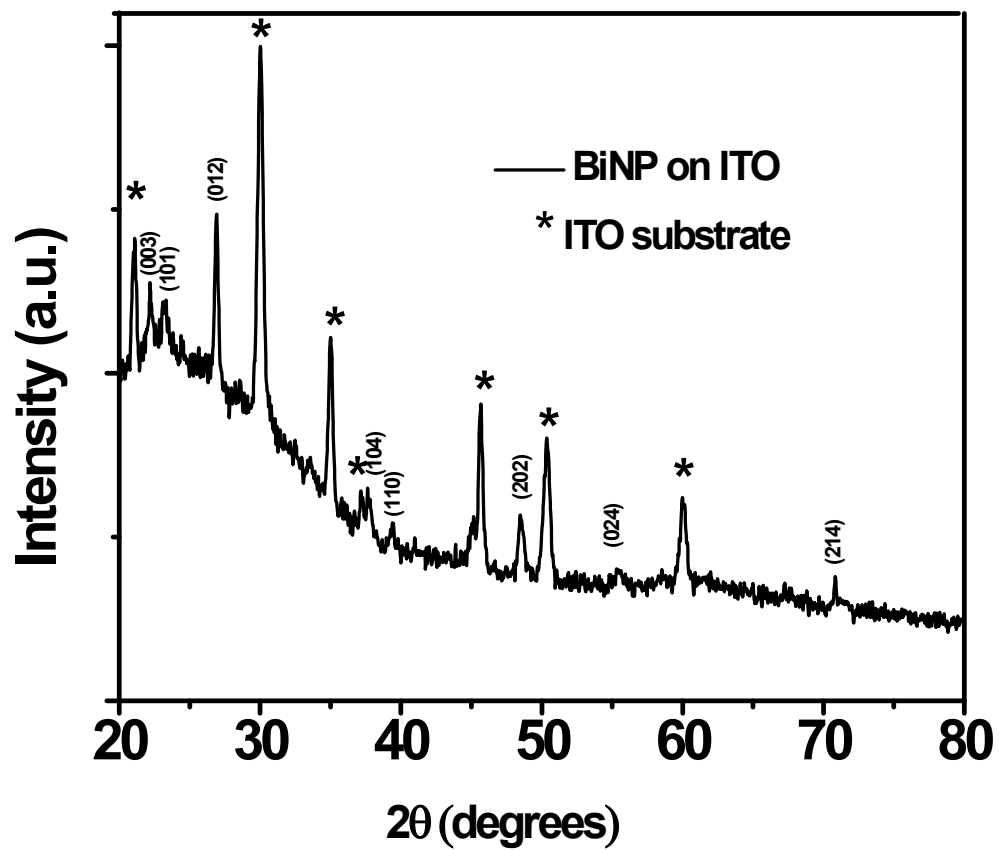


Fig. S8. XRD pattern of BiNP thin film on ITO substrate.

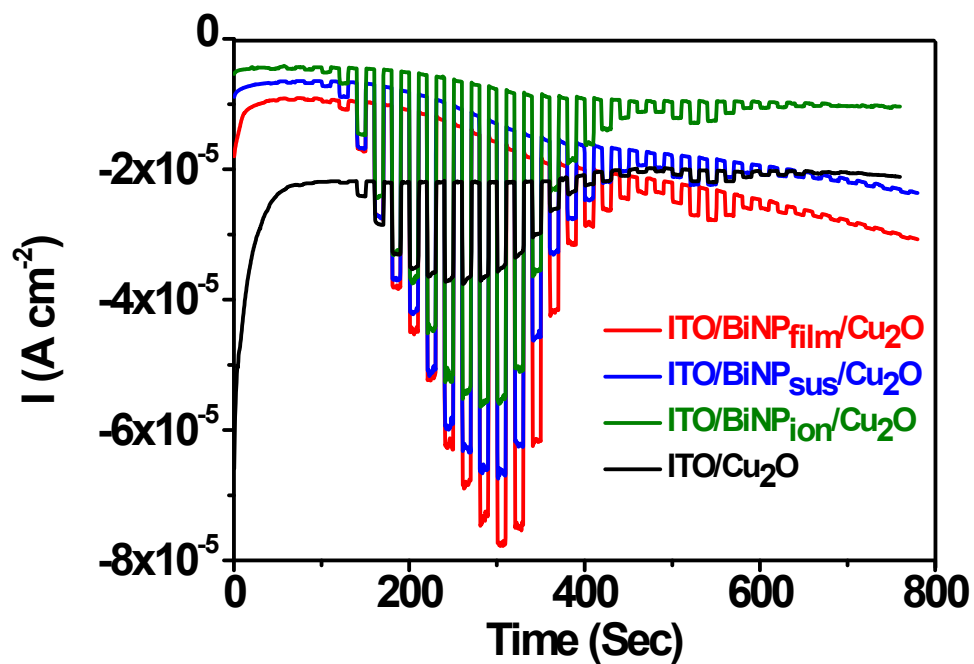


Fig. S9. Photoelectrochemical Action spectrum of Cu₂O thin films on ITO substrates in presence of BiNPs and Bi ion using 0.1 M Na₂SO₄ electrolyte (pH 4.9) at an applied potential of 0.4 V vs RHE.

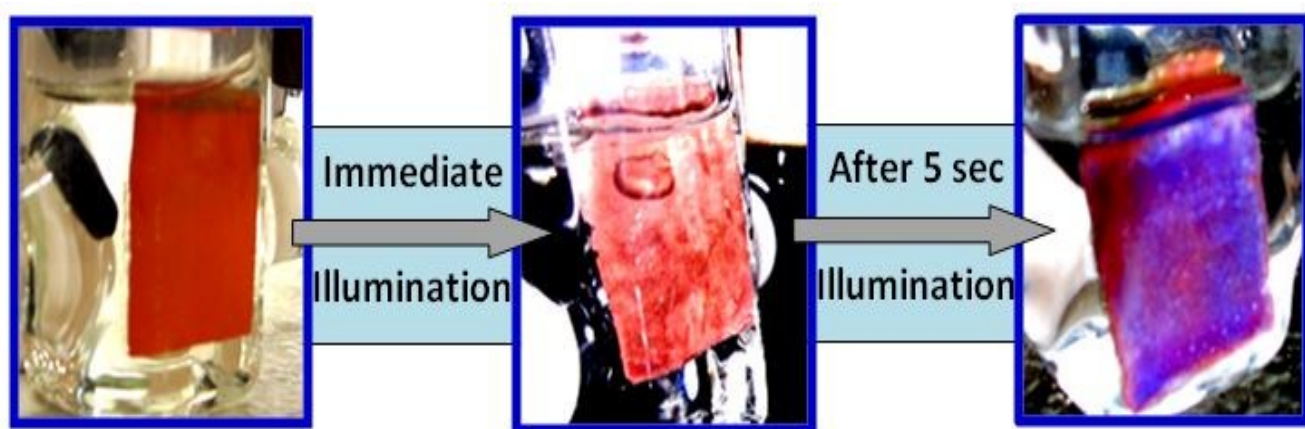


Fig. S10. Photoelectrochemical reduction of methyl viologen (sacrificial reagent)

[$MV^{2+}_{\text{colorless}} \rightarrow MV^{+\bullet}_{\text{deep blue}}$] over ITO/BiNP_{film}/Cu₂O electrodes under illumination.

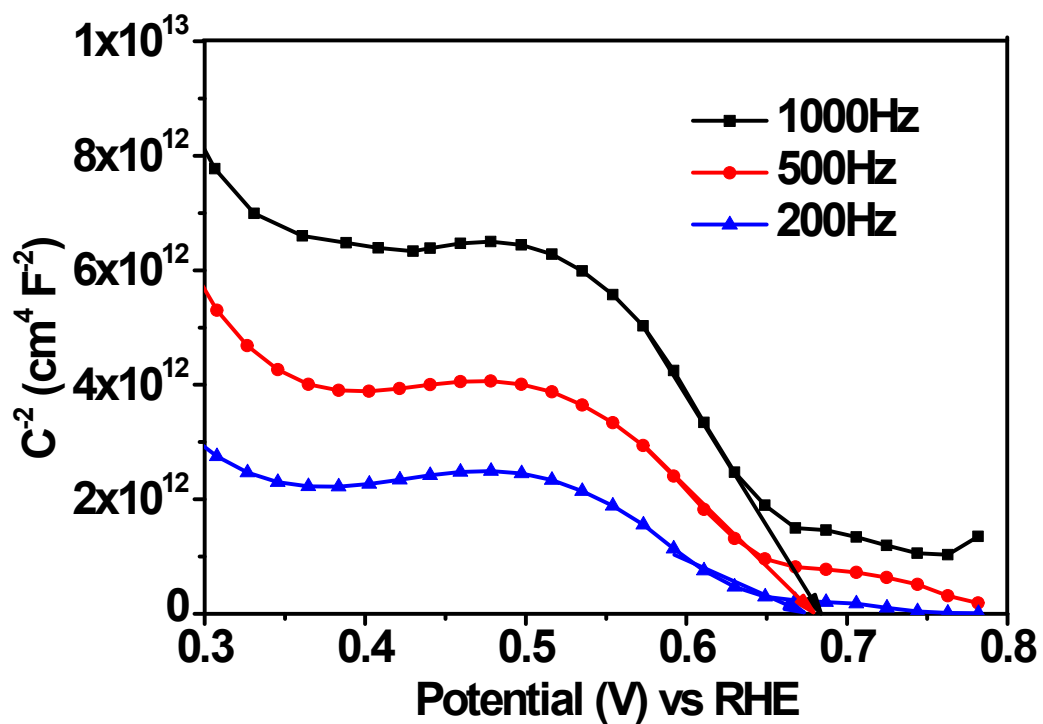


Fig. S11. Mott-Schottky plots of ITO/BiNP_{film}/Cu₂O sample in presence of 0.1 M Na₂SO₄ electrolytes (pH 4.9) using an ac frequencies of 200, 500, and 1000 Hz.

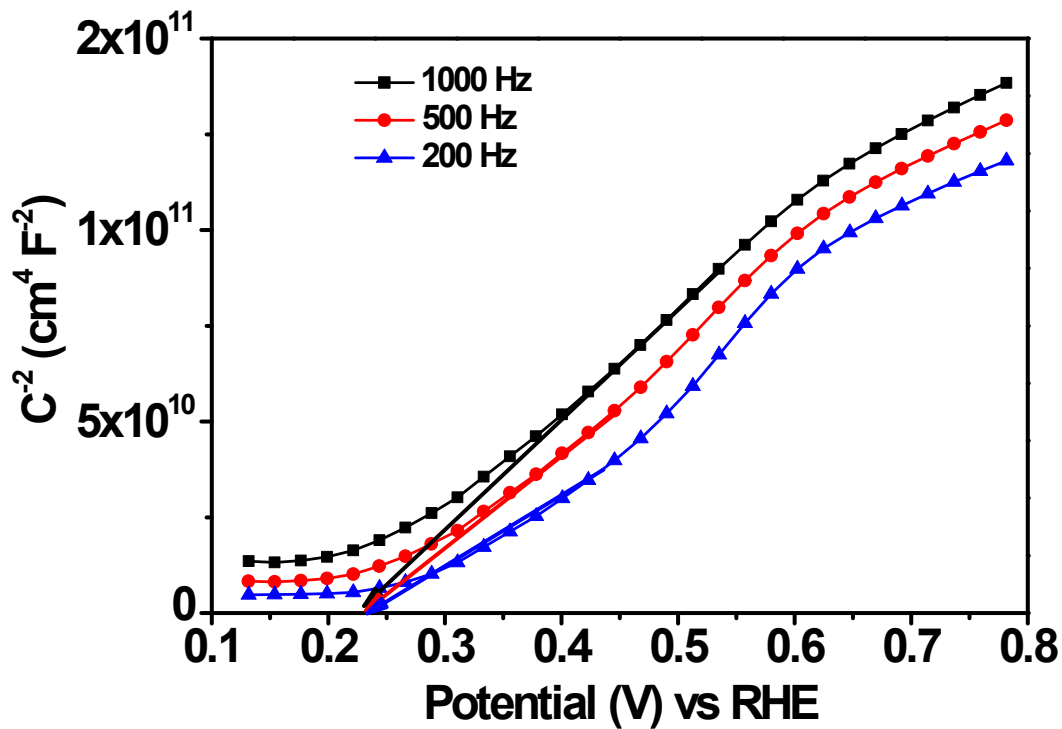


Fig. S12. Mott-Schottky plots of BiNP thin film on ITO in presence of 0.1 M Na_2SO_4 electrolytes (pH 4.9) using an ac frequencies of 200, 500, and 1000 Hz.

Table S1. Variation of atomic percentage of the constituent elements in the Cu₂O thin films developed in presence of BiNP and Bi³⁺ ions.

Sample description	Elements	Atomic%
ITO/BiNP _{film} /Cu ₂ O	Cu	64.34
	O	35.43
	Bi	0.23
ITO/BiNP _{sus} /Cu ₂ O	Cu	64.23
	O	35.56
	Bi	0.21
ITO/Bi _{ion} /Cu ₂ O	Cu	65.49
	O	34.30
	Bi	0.21
ITO/Cu ₂ O	Cu	57.19
	O	42.81
ITO/BiNP	Bi	100

Table S2. Variation of equivalent circuit (EC) parameters of the Cu₂O thin films developed in presence of BiNP and Bi³⁺ ions.

Sample	R _s (Ω)	R _{ct} (Ω)	C _{ct} (F)	Error
ITO/BiNP _{film} /Cu ₂ O	73.28	30.61	2.4 × 10 ⁻⁴	1.51 × 10 ⁻⁹
ITO/BiNP _{sus} /Cu ₂ O	81.14	56.68	9.6 × 10 ⁻⁵	1.60 × 10 ⁻⁹
ITO/Bi _{ion} /Cu ₂ O	86.43	78.84	8.7 × 10 ⁻⁵	1.52 × 10 ⁻⁹
ITO/Cu ₂ O	91.73	128.7	2.3 × 10 ⁻⁵	4.64 × 10 ⁻⁹

Table S.3.: Comparison of photoelectrochemical reduction of water over Cu₂O thin film on conducting glass substrates prepared under different deposition conditions, as available in literature to that with the as prepared Cu₂O, demonstrated in the present report.

Sl. No	References	Substrates	Cu ₂ O synthesized through	Electrolyte for characterization	Light intensity used	Maximum photocurrent density obtained for H ₂ O → H ₂ reaction
01	Present work: Cu ₂ O film developed in presence of (a) BiNP film (b) BiNP suspension (c) Bi³⁺ ion	ITO glass	Electrodeposition	0.1 (M) Na ₂ SO ₄ at pH ~ 4.9	35 mW cm ⁻²	a) -5.2 mA cm⁻² b) -4.9 mA cm⁻² c) -3.7 mA cm⁻²
02	J. Phys. Chem. C, 2012, 116, 7341–7350	100 nm Au and 10 nm Cr adhesion layer coated FTO glass	Electrodeposition	1.0 (M) Na ₂ SO ₄ at pH ~ 4.9	100 mW cm ⁻²	-2.4 mA cm ⁻²
03	J. Mater. Chem., 2012, 22, 2456–2464	Cu coated ITO glass	Electrodeposition followed by anodization	0.5(M) Na ₂ SO ₄ at pH ~ 6.82	100 mW cm ⁻²	-0.37 mA cm ⁻²
04	Int. Journal of Hydrogen Energy, 2008, 33,2897 – 2903	ITO glass	Electrodeposition	0.5 (M) Na ₂ SO ₄	50 mW cm ⁻²	-0.025 mA cm ⁻²
05	Electrochimica Acta, 2012, 62, 1– 7	FTO glass	Electrodeposition	0.1 (M) Na ₂ SO ₄	100 mW cm ⁻²	-0.06 mA cm ⁻²
06	<i>ACS Appl. Mater. Interfaces</i> , 2015, 7, 18344–18352	ITO Glass	Electrodeposition	0.1 (M) Na ₂ SO ₄ at pH ~ 4.9	35 mW cm ⁻²	-2.6 mA cm ⁻²